INNOVATION PARTNERSHIPS
UNIVERSITY OF MICHIGAN

Multi-Bit Memory Read Method

TECHNOLOGY NUMBER: 5256

Technology ID
5256

Category
Hardware
Engineering & Physical Sciences
Semiconductor, MEMS, and Electronics

Inventor
Pinaki Mazumder
Yalcin Yilmaz

Further information
Joohee Kim
jooheek@umich.edu

View online

OVERVIEW

Improved resistive memory device read technology using active devices

- Reduces need for reference resistors and accelerates data access
- Memristor-based crossbar memory, low-power portable electronics, high-density data storage

BACKGROUND

Resistive memory devices, such as memristors, have emerged as promising alternatives to traditional memory technologies, combining fast switching capabilities, indefinite data storage, and high data density. These attributes make them highly appealing for applications ranging from instant-on computers to power-efficient portable electronics. Historically, resistive memory devices have relied on reference resistors and voltage or current sources to detect stored data, which complicates circuit design and increases power consumption. The need for a streamlined, efficient method to read data from resistive memory devices has become increasingly pressing as the demand for faster, more reliable, and energy-efficient memory solutions grows. An improved approach that eliminates the dependency on reference resistors while reducing the complexity of data access operations is crucial to fully harness the potential of resistive memory technology.

INNOVATION

Researchers at the University of Michigan have developed a novel memory read technology for multi-bit resistive memory devices using active devices like diodes. This method involves configuring diodes in series, parallel, or a combination thereof to interpret the intermediate node voltage during memory cell selection. Utilizing a voltage divider configuration between the memory cell and a bias resistor, this innovation circumvents the need for reference resistors or voltage sources, significantly simplifying the read process. Additionally, it reduces the number of comparisons necessary to access stored data, enhancing efficiency. Potential applications of this technology include memristor-based crossbar memory, portable electronics requiring low power, and high-density data storage solutions. This advancement offers a more efficient and streamlined approach to resistive memory, potentially transforming various electronic devices and systems.

ADDITIONAL INFORMATION

US9805791 "Resistive memory structure for single or multi-bit data storage"